DTQ311N03PA www.din-tek.jp

N-Channel 30 V (D-S) MOSFET

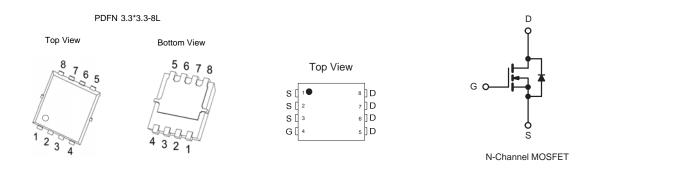
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω) (Typ.)	I _D (A) ^a	Q _g (Typ.)			
30	9 at V _{GS} = 4.5 V	30	4.5 nC			
30	13 at V _{GS} = 2.5 V	30				

FEATURES

- Advanced shielded-gate technology
- · Ultra-low on-resistance and gate-charge
- RoHS compliant
- 100% avalanche tested

APPLICATIONS

- Battery-driven electronic products
- DC-to-DC convertors



ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage	V _{GS}	± 10	V		
Oct 11 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	T _C = 25 °C		30		
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 100 °C	I _D	23	А	
Pulsed Drain Current ^b	I _{DM}	I _{DM} 120			
Single Avalanche Energy	E _{AS}	40	mJ		
Maximum Power Dissipation ^c	T _C = 25 °C	р	22	W	
	T _C = 100 °C	– P _D –	16	vV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	62	°C/W		
Junction-to-Case (Drain)	R _{thJC}	5.8	°C/W		

Notes

a. Calculated continuous current based on maximum allowablejunction temperature.

b. Repetitive rating; pulse width limited by max. junction temperature.

- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of ReuA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	Cymbol			199.	indx.	<u>o</u>
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	30			V
Gate-Source Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.4		1.2	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 10 V$			± 100	nA
	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V			1	
Zero Gate Voltage Drain Current		V _{DS} = 25 V, V _{GS} = 0 V, T _J = 55 °C			10	-μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	Rea()	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		9	11.7	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 10 \text{ A}$		13	17	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 5 V,I _D = 15 A		60		S
Dynamic ^b			•		•	
Input Capacitance	C _{iss}			688		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		305		
Reverse Transfer Capacitance	C _{rss}	1		24		
Total Gate Charge	Qg			4.5		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		1.2		nC
Gate-Drain Charge	Q _{gd}	1		1.3		
Gate Resistance	R _g	f = 1 MHz		3.1		Ω
Turn-On Delay Time	t _{d(on)}			3.5		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, \text{ I}_{D} = 15 \text{ A}, \text{ R}_{g} = 3 \Omega$		3		- ns
Turn-Off DelayTime	t _{d(off)}	V _{GS} = 10 V		15		
Fall Time	t _f	1		3		
Drain -Source Body Diode Characteristic	S		<u> </u>		<u> </u>	<u> </u>
Continous Source-Drain Diode Current	ا _S	T _C = 25 °C			30	A
Pulse Diode Forward Current	I _{SM}				120	
Body Diode Voltage	V _{SD}	I _S = 10 A		0.8		V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, dl/dt = 100 A/μs, Τ _J = 25 °C		15		ns
Body Diode Reverse Recovery Charge	Q _{rr}	F = 20 A, u/ut = 100 A/µs, IJ = 25 C		7		nC

Notes:

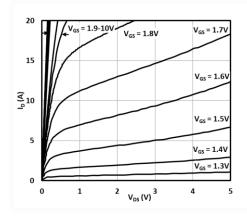
a. Pulse test; pulse width 300 $\mu s,$ duty cycle 2 %.

b. Guaranteed by design, not subject to production testing.

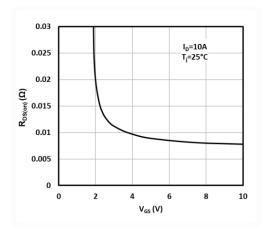
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



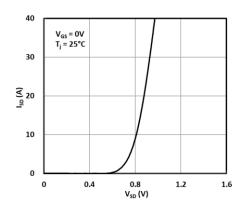
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



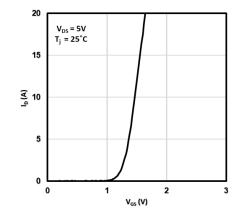
Output Characteristics



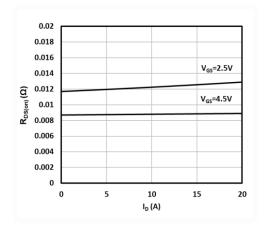
On-resistancevs. gate voltage



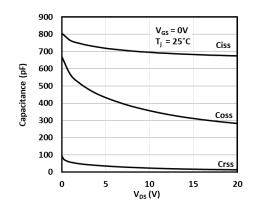
Body Diode Forward Characteristics



Transfer Characteristics



On-resistancevs. drain current



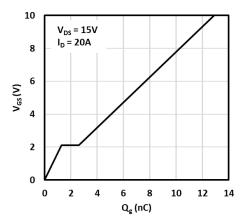
Capacitances



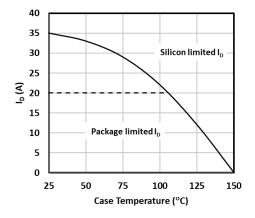
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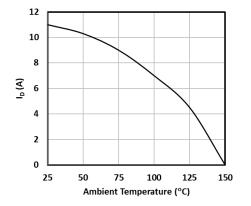
(25 °C, unless otherwise noted)



Gate-to-source voltage vs. gate charge



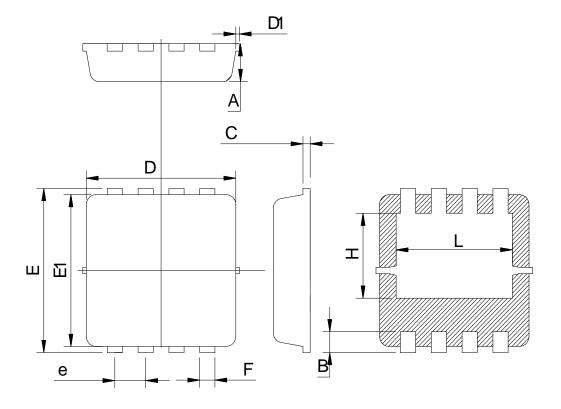
Maximum drain current vs. case temperature



Maximum drain current vs. ambient temperature



PDFN 3.3X3.3 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	0.600	0.775	1.000
В	0.20	0.38	0.55
С	0.05	0.15	0.40
D	3.10	3.25	3.50
D1	-	-	0.15
E	3.15	3.35	3.50
E1	2.60	3.10	3.45
е	0.50	0.65	0.80
F	0.15	0.32	0.45
Н	1.25	1.73	2.10
L	2.20	2.45	2.85

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